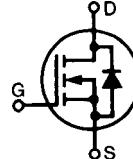


HiPerFET™ Power MOSFETs

N-Channel Enhancement Mode
High dv/dt, Low t_{rr} , HDMOS™ Family

IXFH/IXFT 30N50
IXFH/IXFT 32N50

V_{DSS}	I_{D25}	$R_{DS(on)}$
500 V	30 A	0.16 Ω
500 V	32 A	0.15 Ω

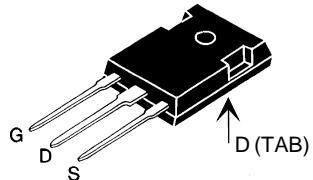


$t_{rr} \leq 250$ ns

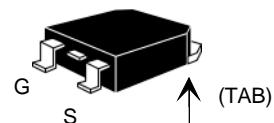
Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V	
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	500	V	
V_{GS}	Continuous	± 20	V	
V_{GSM}	Transient	± 30	V	
I_{D25}	$T_c = 25^\circ\text{C}$	30N50	30	A
		32N50	32	A
I_{DM}	$T_c = 25^\circ\text{C}$ pulse width limited by T_{JM}	30N50	120	A
		32N50	128	A
I_{AR}	$T_c = 25^\circ\text{C}$	30N50	30	A
		32N50	32	A
E_{AS}	$T_c = 25^\circ\text{C}$	1.5	J	
E_{AR}	$I_D = 25^\circ\text{C}$	45	mJ	
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2\text{ }\Omega$	5	V/ns	
P_D	$T_c = 25^\circ\text{C}$	360	W	
T_J		-55 ... +150	$^\circ\text{C}$	
T_{JM}		150	$^\circ\text{C}$	
T_{stg}		-55 ... +150	$^\circ\text{C}$	
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$	
M_d	Mounting torque	1.13/10	Nm/lb.in.	
Weight		6	g	

Symbol	Test Conditions	Characteristic Values		
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$ V_{DSS} temperature coefficient	500		V
			0.102	%/K
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4\text{ mA}$ $V_{GS(th)}$ temperature coefficient	2	4	V
			-0.206	%/K
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$	± 100		nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	200	μA mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 15\text{ A}$ Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$	32N50 30N50	0.15 0.16	Ω

TO-247 AD (IXFH)



TO-268 (D3) Case Style



G = Gate,
S = Source,
TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- Fast intrinsic Diode

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls

Advantages

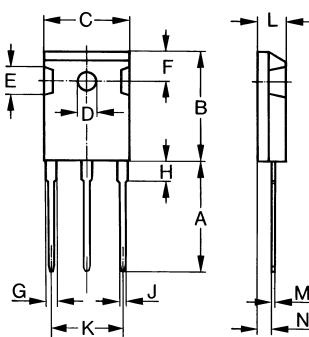
- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

Symbol Test Conditions

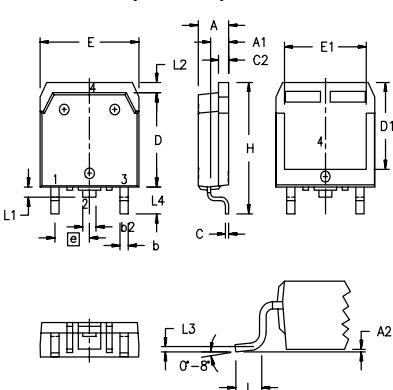
		Characteristic Values		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10 \text{ V}; I_D = 0.5 I_{D25}$, pulse test	18	28	S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	5200	5700	pF
		640	750	pF
		240	310	pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2 \Omega$ (External)	35	45	ns
		42	50	ns
		110	140	ns
		26	35	ns
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$	227	300	nC
		29	40	nC
		110	145	nC
R_{thJC}	(TO-247 Case Style)	0.25	0.35	K/W
R_{thCK}			0.25	K/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
		min.	typ.	max.
I_s	$V_{GS} = 0 \text{ V}$	30N50		A
		32N50		A
I_{SM}	Repetitive; pulse width limited by T_{JM}	30N50	120	A
		32N50	128	A
V_{SD}	$I_F = I_s, V_{GS} = 0 \text{ V},$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$		1.5	V
t_{rr} Q_{RM} I_{RM}	$I_F = I_s$ $-di/dt = 100 \text{ A}/\mu\text{s},$ $V_R = 100 \text{ V}$	$T_j = 25^\circ\text{C}$	250	ns
		$T_j = 125^\circ\text{C}$	400	ns
		$T_j = 25^\circ\text{C}$	0.85	μC
		$T_j = 25^\circ\text{C}$	8	A

TO-247 AD (IXFH) Outline

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

TO-268AA (D³ PAK)

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₂	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45	BSC	.215	BSC
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3	0.25	BSC	.010	BSC
L4	3.80	4.10	.150	.161

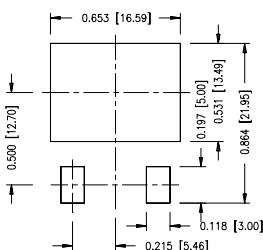
Min. Recommended Footprint

Figure 1. Output Characteristics at 25°C

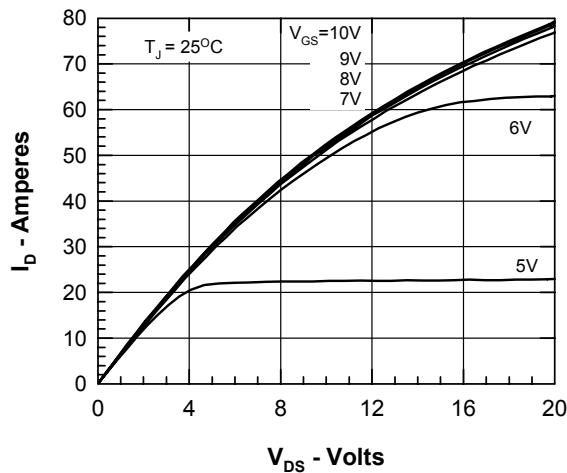


Figure 3. $R_{DS(on)}$ normalized to 15A/25°C vs. I_D

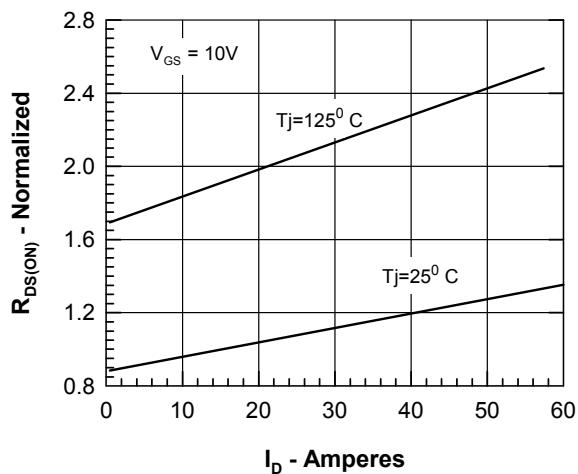


Figure 5. Drain Current vs. Case Temperature

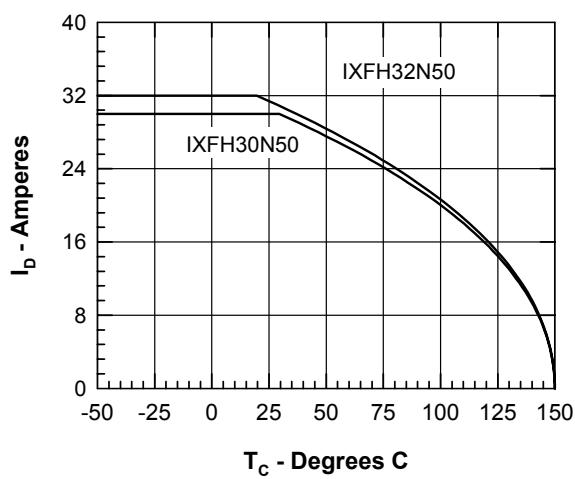


Figure 2. Output Characteristics at 125°C

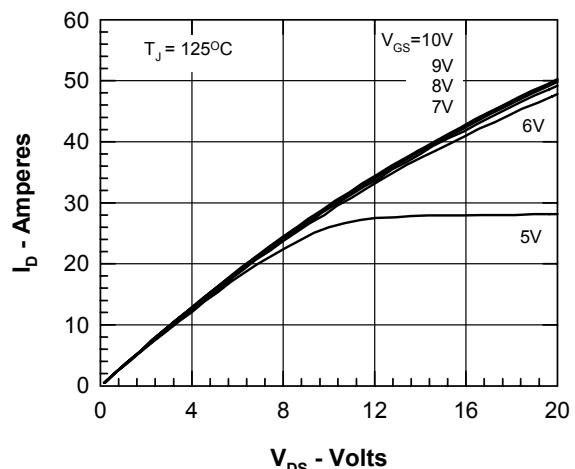


Figure 4. $R_{DS(on)}$ normalized to 15A/25°C vs. T_j

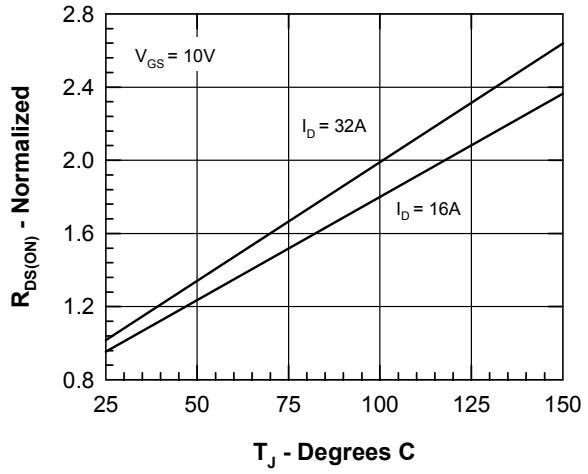


Figure 6. Admittance Curves

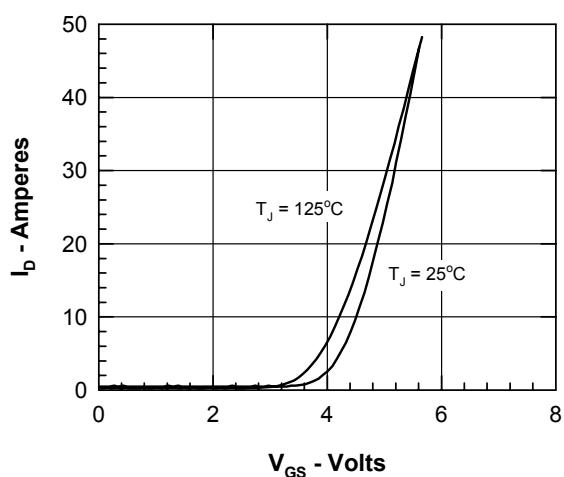


Figure 7. Gate Charge

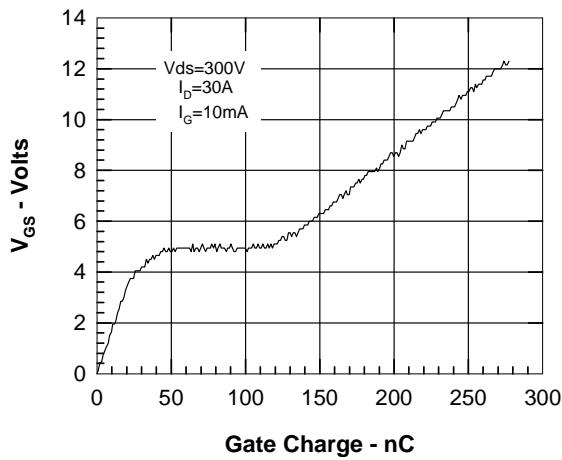


Figure 8. Capacitance Curves

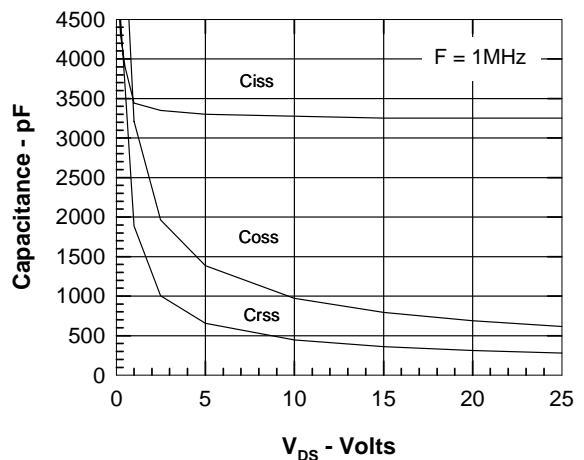


Figure 9. Forward Voltage Drop of the Intrinsic Diode

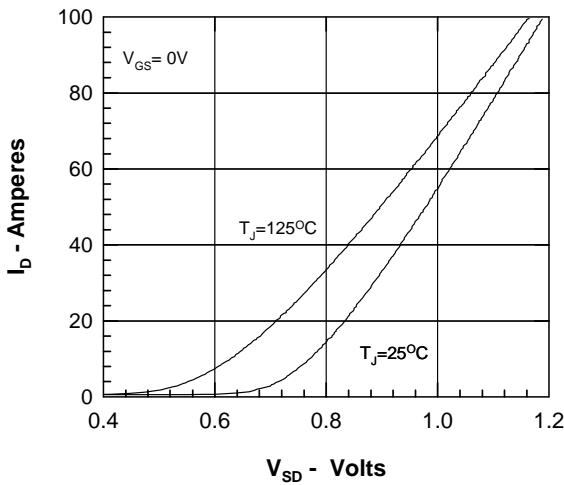
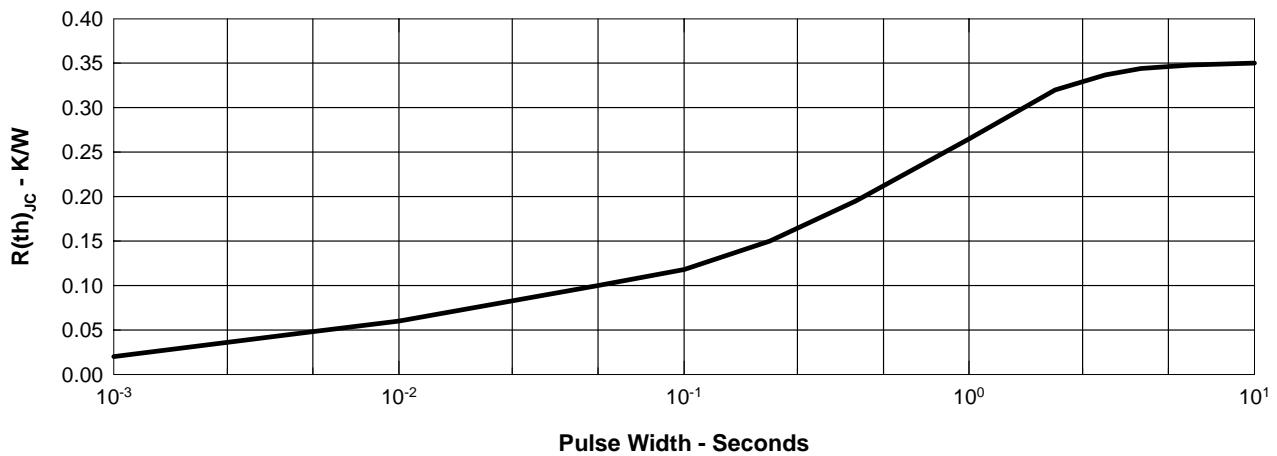


Figure 10. Transient Thermal Resistance



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